



N-Channel 16-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
16	0.0033 at $V_{GS} = 4.5 \text{ V}$	25		
	0.0055 at V _{GS} = 2.5 V	20		

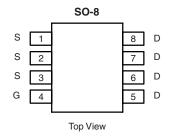
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFETs: 2.5 V Rated
- Low 3.3 mΩ R_{DS(on)}
- · Low Gate Resistance
- 100 % R_g Tested

ROHS COMPLIANT HALOGEN FREE Available

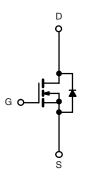
APPLICATIONS

- · Synchronous Rectification
- Low Output Voltage Synchronous Rectification



Ordering Information: Si4862DY-T1-E3 (Lead (Pb)-free)

Si4862DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25$ °C, unles	ss otherwise n	oted		_
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	16		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Dunin Courset /T 450 00\8	T _A = 25 °C	- I _D	25	17	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		20	13	
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	60		Α
Continuous Source Current (Diode Conduction) ^a		I _S	2.9	1.3	
	T _A = 25 °C	D.	3.5	1.6	W
Maximum Power Dissipation ^a	T _A = 70 °C	P_{D}	2.2	1	VV
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55	5 to 150	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	29	35		
	Steady State	□ □thJA	67	80	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	13	16		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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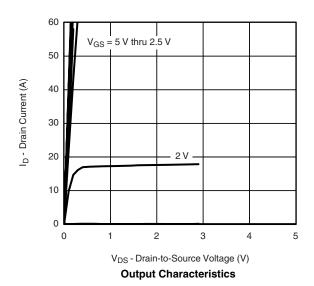
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	ool Test Conditions		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6			٧	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zava Cata Valtaga Drain Current		V _{DS} = 12.8 V, V _{GS} = 0 V			1	μА	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 12.8 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
D : 0	В	$V_{GS} = 4.5 \text{ V}, I_D = 25 \text{ A}$		0.0027 0.0033	0		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 20 \text{ A}$		0.0045	0.0055	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 6 V, I _D = 25 A		140		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 2.9 A, V _{GS} = 0 V		0.75	1.1	٧	
Dynamic ^b							
Total Gate Charge	Q_g			48	70		
Gate-Source Charge	Q_{gs}	$V_{DS} = 6 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 25 \text{ A}$		11.8		nC	
Gate-Drain Charge	Q_{gd}			8.9			
Gate Resistance	R_g		0.5	1.3	2.2	Ω	
Turn-On Delay Time	t _{d(on)}			42	60		
Rise Time	t _r	V_{DD} = 6 V, R_L = 6 Ω		38	60		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 4.5 V, R_g = 6 Ω		120	180	ns	
Fall Time	t _f			50	75		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.9 A, dI/dt = 100 A/μs		80	120		

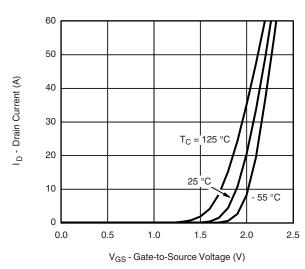
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

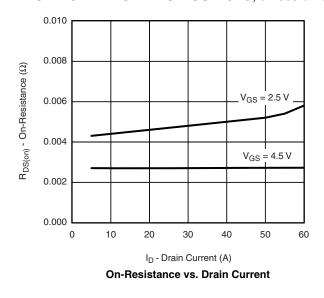


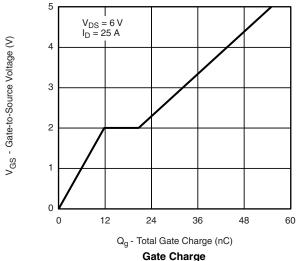


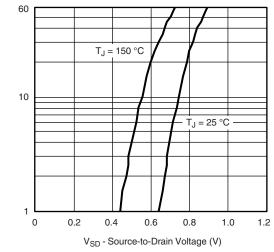




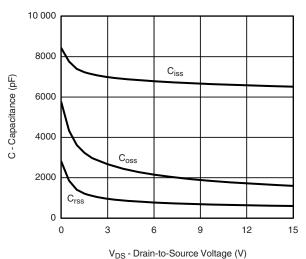
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



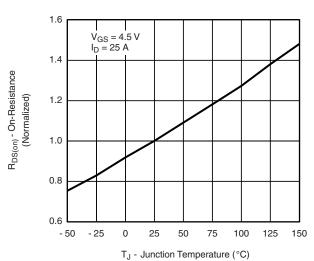




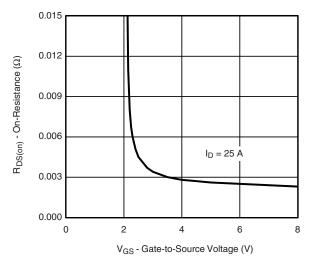
Source-Drain Diode Forward Voltage



Capacitance



On-Resistance vs. Junction Temperature



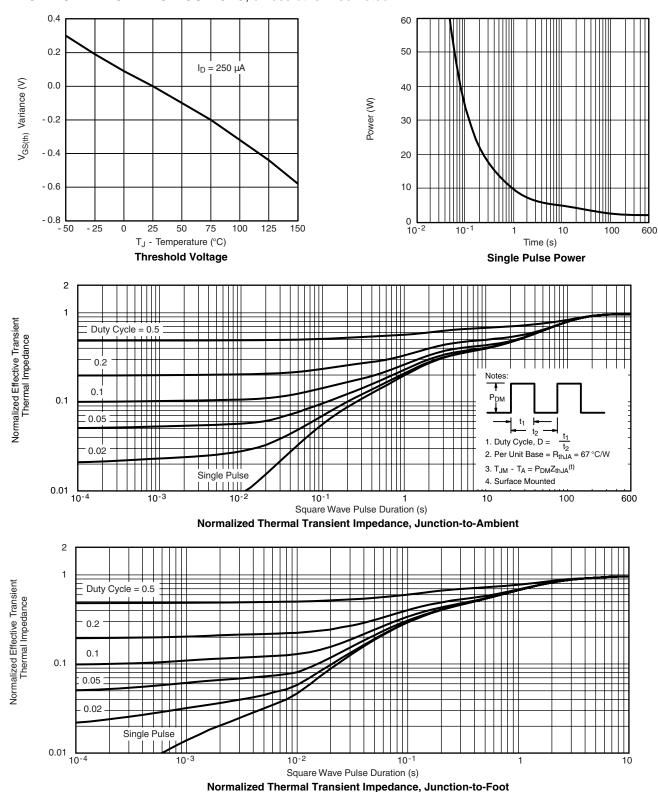
On-Resistance vs. Gate-to-Source Voltage

Is - Source Current (A)

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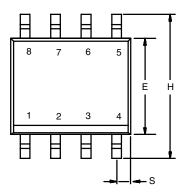
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050) BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
FCN: C-06527-Bey 11-Sen-06						

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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